



SDI FINAL EVALUATION FORM 1.1

PART 1:

Journal Name:	Physical Science International Journal
Manuscript Number:	Ms_PSIJ_29024
Title of the Manuscript:	Influence of Annealing Temperature on the Physical Properties of Polycrystalline Cu ₂ SnSe ₃ Thin Films Prepared by Thermal Vacuum Evaporation Technique
Type of Article:	Original Research Article

PART 2:

FINAL EVALUATOR'S comments on revised paper (if any)	Authors' response to final evaluator's comments
Unfortunately, I did not see obvious improvements in the revised manuscript. One thing should be pointed out is EDX is not very accurate when comes to element analysis. A smooth surface is needed for element quantity analysis. However, drastic change in top surface morphology has been clearly observed from SEM. Also, it is hard to believe a >10% change in Cu percentage in the CIS alloy. Cu is much more stable than In and Se. It is impossible to have Cu evaporation at such a low temperature. 500°C-sulfurized CIS based photovoltaic cells have been reported to show increased efficiency. Thermal stability of CIS has been widely studied and authors should read related literatures . (J Nanosci Nanotechnol. 2014 Dec;14,12:9313-8; J. Electrochem. Soc. 2015volume 162, issue 1, D36-D41; DOI: 10.1002/pssa.201431232 DOI: 10.1007/s00339-013-8146-9)	

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